

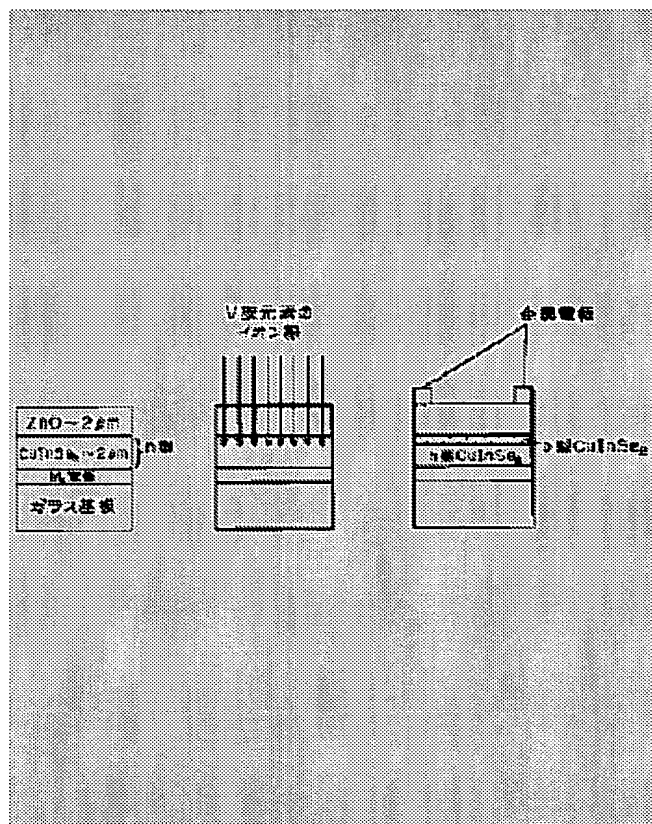
HOMOJUNCTION SEMICONDUCTOR DEVICE AND MANUFACTURE OF PHOTOELECTRIC CONVERSION DEVICE USING THE SAME

Patent number: JP6097481
Publication date: 1994-04-08
Inventor: FURUBIKI SHIGEMI; NEGAMI TAKAYUKI; NISHITANI MIKIHICO; WADA TAKAHIRO
Applicant: MATSUSHITA ELECTRIC IND CO LTD
Classification:
- **international:** H01L31/04
- **europaen:**
Application number: JP19920244375 19920914
Priority number(s): JP19920244375 19920914

Report a data error here

Abstract of JP6097481

PURPOSE: To provide a homojunction semiconductor device having an improved device characteristic, which can be matched with the semiconductor thin film made of I-III-(IV)₂ chalcopyrite compound in its lattice constant, its orientation quality to substrate surface and its surface morphology and to provide a photoelectric conversion semiconductor device using the same.
CONSTITUTION: On an Mo lower electrode, an element having CuInSe₂, ZnO and ITO thin films is manufactured. An ionic radiation of nitrogen atom is acceleration-projected thereon, and a homojunction is formed in the CuInSe₂ thin film, and thereby, a photoelectric conversion semiconductor device is created.



Data supplied from the *esp@cenet* database - Worldwide